BL GALAXY ELECTRICAL

RM11A(Z)---RM11C(Z)

PLASTIC SILICON RECTIFIER

VOLTAGE RANGE: 600 --- 1000 V
CURRENT: 1.2 A

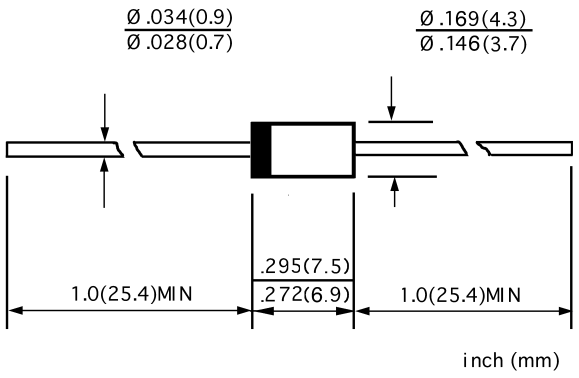
FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned witn Freon,Alcohol,Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case:JEDEC DO-15L,molded plastic
- ◇ Terminals: Axial lead ,solderable per MIL- STD-202,Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.017 ounces,0.48 grams
- ◇ Mounting position: Any

DO - 15L



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		RM11A	RM11B	RM11C	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	600	800	1000	V
Maximum RMS voltage	V_{RMS}	420	560	700	V
Maximum DC blocking voltage	V_{DC}	600	800	1000	V
Maximum average forw ard rectified current 9.5mm lead length, @T_A=75℃	$I_{F(AV)}$	1.2			A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load @T_J=125℃	I_{FSM}	100.0			A
Maximum instantaneous forw ard voltage @ 1.5 A	V_F	0.92			V
Maximum reverse current @T_A=25℃ at rated DC blocking voltage @T_A=100℃	I_R	5.0 50.0			μA
Typical junction capacitance (Note1)	C_J	25			pF
Typical thermal resistance (Note2)	$R_{\theta JA}$	30			℃/W
Operating junction temperature range	T_J	-55-----+150			℃
Storage temperature range	T_{STG}	-55-----+150			℃

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Thermal resistance from junction to ambient.

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FIG.1 -- FORWARD DERATING CURVE

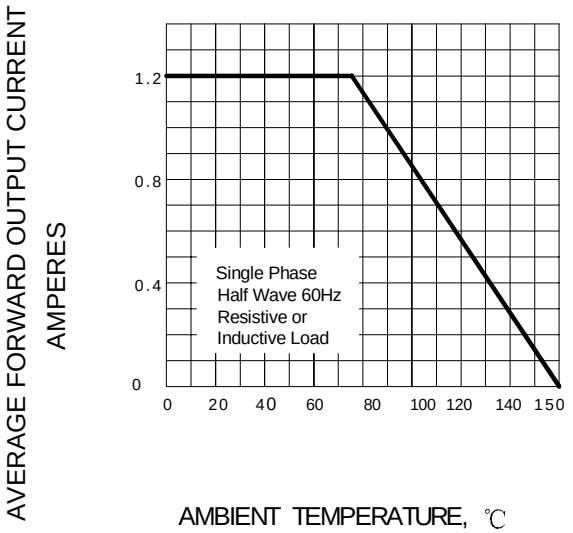


FIG.2 -- PEAK FORWARD SURGE CURRENT

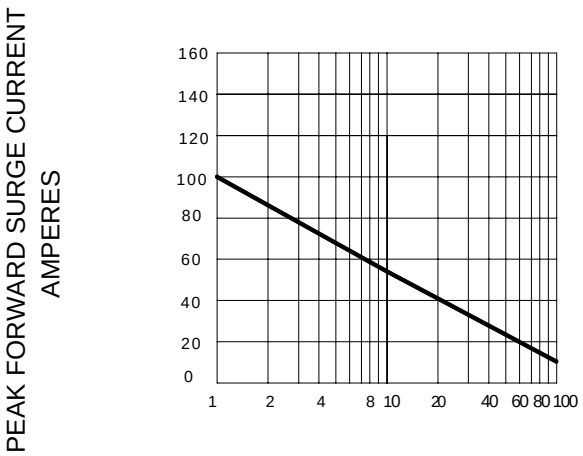


FIG.3 -- TYPICAL FORWARD CHARACTERISTIC

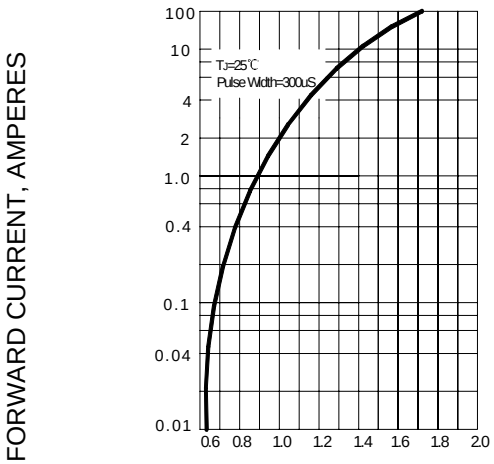


FIG.4 -- TYPICAL REVERSE CHARACTERISTICS

